

# Shi Liu

## List of Publications by Year in descending order

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33  
papers

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citations

623734

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752698

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docs citations

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times ranked

899  
citing authors

#	ARTICLE	IF	CITATIONS
1	Ultralow Interface Recombination Velocity ( $\sim 1$ cm/s) at CdTe/MgCd $\text{Te}$ Heterointerface. IEEE Journal of Photovoltaics, 2017, 7, 913-918.	2.5	8
2	Ultralow interface recombination velocity ( $\sim 1$ cm/s) in CdTe/Mg $\text{Te}$ /Cd $\text{Te}$ double-heterostructures. , 2016, , .		1
3	Monocrystalline CdTe solar cells with open-circuit voltage over 1â€‰%V and efficiency of 17%. Nature Energy, 2016, 1, .	39.5	172
4	Can liquid metal flow in microchannels made of its own oxide skin?. Microfluidics and Nanofluidics, 2016, 20, 1.	2.2	27
5	Electrical and Optical Properties of n-Type Indium-Doped CdTe/Mg $_{0.46}$ Cd $_{0.54}$ Te Double Heterostructures. IEEE Journal of Photovoltaics, 2016, 6, 552-556.	2.5	20
6	Structural and optical properties of Mg $_x$ Cd $_{1-x}$ Te alloys grown on InSb (100) substrates using molecular beam epitaxy. , 2015, , .		0
7	Minority carrier lifetime of lattice-matched CdZnTe alloy grown on InSb substrates using molecular beam epitaxy. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2015, 33, .	1.2	14
8	Influence of carrier localization on minority carrier lifetime in InAs/InAsSb type-II superlattices. Applied Physics Letters, 2015, 107, 201107.	3.3	34
9	Measurement of InAsSb bandgap energy and InAs/InAsSb band edge positions using spectroscopic ellipsometry and photoluminescence spectroscopy. Journal of Applied Physics, 2015, 118, .	2.5	70
10	Carrier lifetimes and interface recombination velocities in CdTe/Mg $_x$ Cd $_{1-x}$ Te double heterostructures with different Mg compositions grown by molecular beam epitaxy. Applied Physics Letters, 2015, 107, .	3.3	25
11	Study of carrier lifetime degradation in (Zn)CdTe/MgCdTe double heterostructures. , 2015, , .		0
12	Optical properties of indium-doped CdTe/MgCdTe double heterostructures. , 2015, , .		1
13	An indirect method of studying band alignments in nBn photodetectors using off-axis electron holography. Applied Physics Letters, 2015, 107, .	3.3	6
14	Monocrystalline ZnTe/CdTe/MgCdTe double heterostructure solar cells grown on InSb substrates. , 2015, , .		2
15	Significantly improved carrier lifetime and reduced interface recombination velocity for CdTe/MgCdTe double heterostructures. , 2015, , .		2
16	Absorption properties of type-II InAs/InAsSb superlattices measured by spectroscopic ellipsometry. Applied Physics Letters, 2015, 106, .	3.3	31
17	Ultra-thin GaAs single-junction solar cells integrated with a reflective back scattering layer. Journal of Applied Physics, 2014, 115, .	2.5	57
18	Carrier Decay and Diffusion Dynamics in Single-Crystalline CdTe as Seen via Microphotoluminescence. Physical Review Applied, 2014, 2, .	3.8	15

#	ARTICLE	IF	CITATIONS
19	Characterization and quantitative analysis of ultra-thin GaAs single-junction solar cells with reflective back scattering. , 2014, , .		1
20	Determination of CdTe bulk carrier lifetime and interface recombination velocity of CdTe/MgCdTe double heterostructures grown by molecular beam epitaxy. Applied Physics Letters, 2014, 105, .	3.3	49
21	Molecular beam epitaxy using bismuth as a constituent in InAs and a surfactant in InAs/InAsSb superlattices. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, .	1.2	25
22	Time-resolved and excitation-dependent photoluminescence study of CdTe/MgCdTe double heterostructures grown by molecular beam epitaxy. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, .	1.2	33
23	Temperature-dependent time-resolved photoluminescence study of monocrystalline CdTe/MgCdTe double heterostructures with low defect density. , 2014, , .		1
24	In situ FIB-SEM Experimentation: from Nanoscale Wetting to Nanofabrication of Gallium-based Liquid Metals. Microscopy and Microanalysis, 2014, 20, 320-321.	0.4	0
25	Impact of substrate temperature on the structural and optical properties of strain-balanced InAs/InAsSb type-II superlattices grown by molecular beam epitaxy. Applied Physics Letters, 2013, 102, .	3.3	11
26	A calibration method for group V fluxes and impact of V/III flux ratio on the growth of InAs/InAsSb type-II superlattices by molecular beam epitaxy. Journal of Crystal Growth, 2013, 378, 145-149.	1.5	11
27	Growth, steady-state, and time-resolved photoluminescence study of CdTe/MgCdTe double heterostructures on InSb substrates using molecular beam epitaxy. Applied Physics Letters, 2013, 103, .	3.3	56
28	SiO <sub>2</sub> /ZnSe anti-reflection coating for solar cells. , 2013, , .		2
29	CdSe/CdTe type-II superlattices grown on GaSb (001) substrates by molecular beam epitaxy. Applied Physics Letters, 2012, 100, .	3.3	4
30	Approaching single-junction theoretical limit using ultra-thin GaAs solar cells with optimal optical designs. , 2012, , .		7
31	Long-wave infrared nBn photodetectors based on InAs/InAsSb type-II superlattices. Applied Physics Letters, 2012, 101, .	3.3	117
32	Ultra-thin GaAs single-junction solar cells integrated with lattice-matched ZnSe as a reflective back scattering layer. , 2012, , .		3
33	II-VI/III-V integration for next generation multi-junction solar cells. , 2011, , .		0